

MOSFETs Silicon N-channel MOS (U-MOSVII-H)

TPN2010FNH

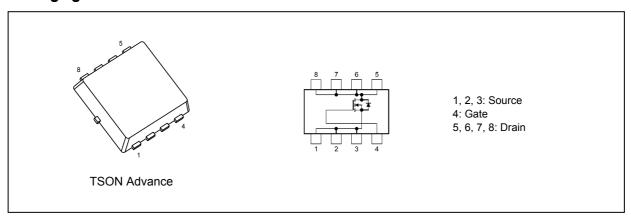
1. Applications

- · High-Efficiency DC-DC Converters
- Switching Voltage Regulators

2. Features

- (1) High-speed switching
- (2) Small gate charge: $Q_{SW} = 2.6 \text{ nC (typ.)}$
- (3) Low drain-source on-resistance: $R_{DS(ON)} = 168 \text{ m}\Omega$ (typ.) ($V_{GS} = 10 \text{ V}$)
- (4) Low leakage current: I_{DSS} = 10 μA (max) (V_{DS} = 250 V)
- (5) Enhancement mode: V_{th} = 2.0 to 4.0 V (V_{DS} = 10 V, I_{D} = 0.2 mA)

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) (Ta = 25 °C unless otherwise specified)

| Characteris | tics | | Symbol | Rating | Unit |
|-------------------------------|--------------------------|--------------------|------------------|------------|------|
| Drain-source voltage | | | V_{DSS} | 250 | V |
| Gate-source voltage | | | V _{GSS} | ±20 | |
| Drain current (DC) | (Silicon limit) | (Note 1), (Note 2) | I _D | 9.9 | Α |
| Drain current (DC) | (Continuous) | (Note 1) | I _D | 5.6 | |
| Drain current (pulsed) | (t = 1 ms) | (Note 1) | I _{DP} | 19 | |
| Power dissipation | (T _c = 25 °C) | | P_{D} | 39 | W |
| Power dissipation | (t = 10 s) | (Note 3) | P _D | 1.9 | |
| Power dissipation | (t = 10 s) | (Note 4) | P_{D} | 0.7 | |
| Single-pulse avalanche energy | | (Note 5) | E _{AS} | 34 | mJ |
| Avalanche current | | | I _{AR} | 5.6 | Α |
| Channel temperature | | | T _{ch} | 150 | °C |
| Storage temperature | | | T _{stg} | -55 to 150 | |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Start of commercial production



5. Thermal Characteristics

| Characteristics | Symbol | Max | Unit | | |
|---------------------------------------|--------------------------|----------|-----------------------|------|------|
| Channel-to-case thermal resistance | (T _c = 25 °C) | | R _{th(ch-c)} | 3.20 | °C/W |
| Channel-to-ambient thermal resistance | (t = 10 s) | (Note 3) | R _{th(ch-a)} | 65.7 | |
| Channel-to-ambient thermal resistance | (t = 10 s) | (Note 4) | R _{th(ch-a)} | 178 | |

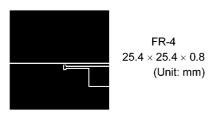
Note 1: Ensure that the channel temperature does not exceed 150 °C.

Note 2: Limited by silicon chip capability.

Note 3: Device mounted on a glass-epoxy board (a), Figure 5.1

Note 4: Device mounted on a glass-epoxy board (b), Figure 5.2

Note 5: V_{DD} = 60 V, T_{ch} = 25 °C (initial), L = 1.8 mH, I_{AR} = 5.6 A



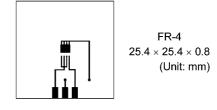


Fig. 5.1 Device Mounted on a Glass-Epoxy Board (a)

Fig. 5.2 Device Mounted on a Glass-Epoxy Board (b)

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

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6. Electrical Characteristics

6.1. Static Characteristics (T_a = 25 °C unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|--------------------------------|----------------------|---|-----|------|------|------|
| Gate leakage current | I _{GSS} | $V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$ | _ | _ | ±0.1 | μА |
| Drain cut-off current | I _{DSS} | V _{DS} = 250 V, V _{GS} = 0 V | _ | _ | 10 | |
| Drain-source breakdown voltage | V _{(BR)DSS} | I _D = 10 mA, V _{GS} = 0 V | 250 | _ | | V |
| | V _{(BR)DSX} | $I_D = 10 \text{ mA}, V_{GS} = -20 \text{ V}$ | 175 | _ | | |
| Gate threshold voltage | V_{th} | $V_{DS} = 10 \text{ V}, I_{D} = 0.2 \text{ mA}$ | 2.0 | _ | 4.0 | |
| Drain-source on-resistance | R _{DS(ON)} | $V_{GS} = 10 \text{ V}, I_D = 2.8 \text{ A}$ | _ | 168 | 198 | mΩ |

6.2. Dynamic Characteristics ($T_a = 25$ °C unless otherwise specified)

| Characteristics | Symbol | Test Condition | | Тур. | Max | Unit |
|--------------------------------|------------------|---|---|------|-----|------|
| Input capacitance | C _{iss} | V _{DS} = 100 V, V _{GS} = 0 V, f = 1 MHz | _ | 460 | 600 | pF |
| Reverse transfer capacitance | C _{rss} | | _ | 3.0 | 50 | |
| Output capacitance | C _{oss} | | _ | 45 | _ | |
| Gate resistance | r _g | _ | _ | 4.0 | 6.0 | Ω |
| Switching time (rise time) | t _r | See Fig. 6.2.1 | _ | 5.2 | _ | ns |
| Switching time (turn-on time) | t _{on} | | _ | 14 | _ | |
| Switching time (fall time) | t _f | | _ | 4.5 | _ | |
| Switching time (turn-off time) | t _{off} | | | 19 | | |

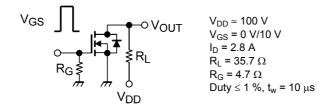


Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics (T_a = 25 °C unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|---|------------------|--|-----|------|-----|------|
| Total gate charge (gate-source plus gate-drain) | Qg | $V_{DD} \approx 100 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 5.6 \text{ A}$ | _ | 7.0 | | nC |
| Gate-source charge 1 | Q _{gs1} | | | 2.4 | | nC |
| Gate-drain charge | Q_{gd} | | _ | 1.5 | | |
| Gate switch charge | Q_{SW} | | | 2.6 | | |

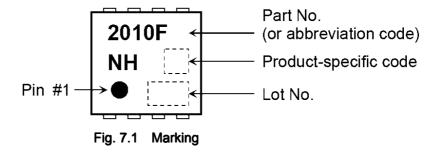
6.4. Source-Drain Characteristics (T_a = 25 °C unless otherwise specified)

| Characteristics | | Symbol | Test Condition | Min | Тур. | Max | Unit |
|--------------------------------|----------|------------------|--|-----|------|------|------|
| Reverse drain current (pulsed) | (Note 6) | I _{DRP} | _ | _ | _ | 19 | Α |
| Diode forward voltage | | V_{DSF} | I _{DR} = 5.6 A, V _{GS} = 0 V | 1 | | -1.2 | V |

Note 6: Ensure that the channel temperature does not exceed 150 °C.



7. Marking



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8. Characteristics Curves (Note)

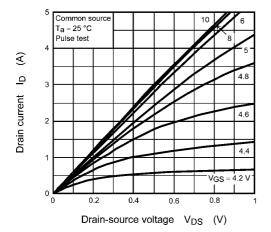


Fig. 8.1 I_D - V_{DS}

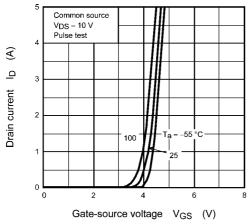


Fig. 8.3 I_D - V_{GS}

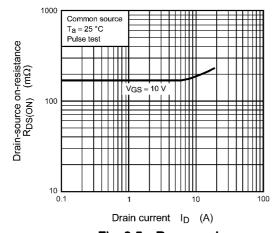


Fig. 8.5 R_{DS(ON)} - I_D

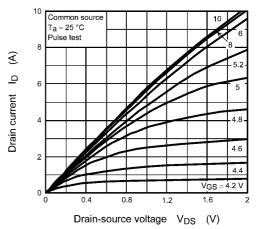


Fig. 8.2 I_D - V_{DS}

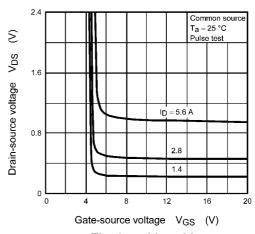


Fig. 8.4 $V_{DS} - V_{GS}$

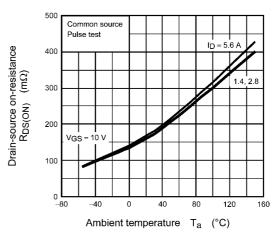


Fig. 8.6 R_{DS(ON)} - T_a

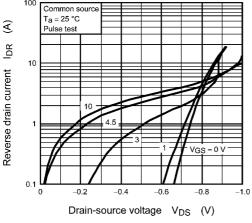
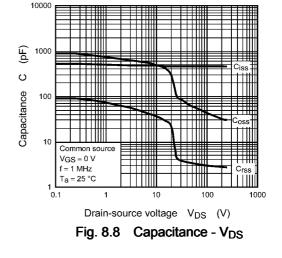


Fig. 8.7 I_{DR} - V_{DS}



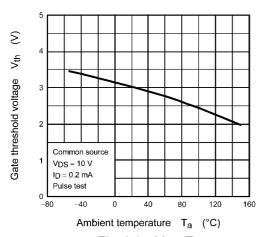


Fig. 8.9 V_{th} - T_a

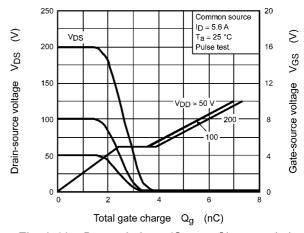


Fig. 8.10 Dynamic Input/Output Characteristics

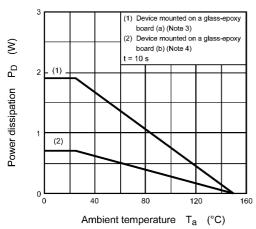


Fig. 8.11 P_D - T_a (Guaranteed Maximum)

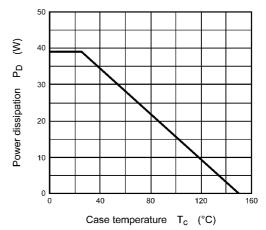


Fig. 8.12 P_D - T_c (Guaranteed Maximum)

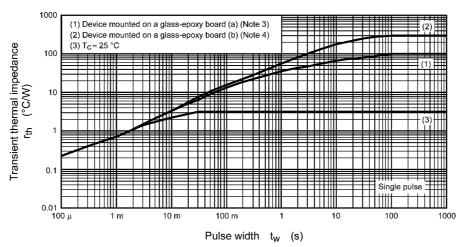


Fig. 8.13 r_{th} - t_w (Guaranteed Maximum)

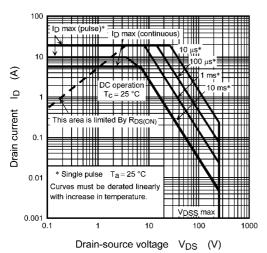


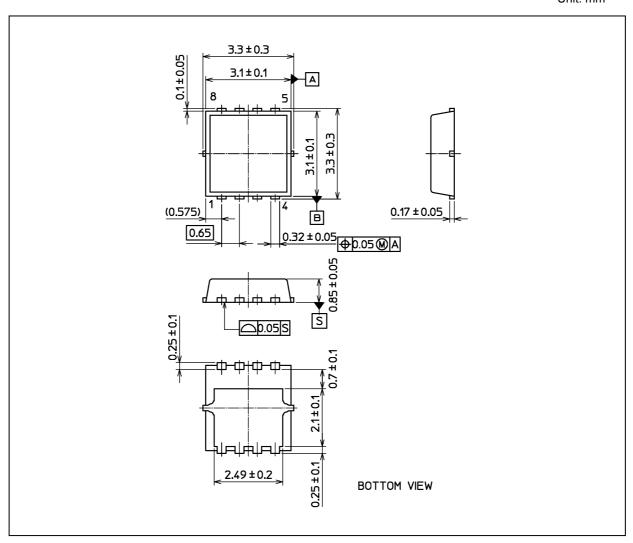
Fig. 8.14 Safe Operating Area (Guaranteed Maximum)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



Package Dimensions

Unit: mm



Weight: 0.02 g (typ.)

| Package Name(s) | |
|------------------------|--|
| TOSHIBA: 2-3X1S | |
| Nickname: TSON Advance | |

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